N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low-On Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

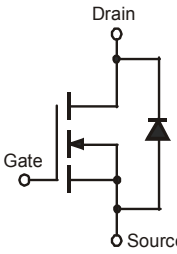
Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)

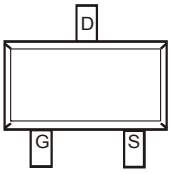
SOT-323



TOP VIEW



Equivalent Circuit



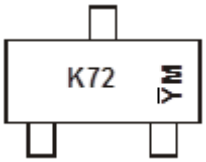
TOP VIEW

Ordering Information (Notes 4)

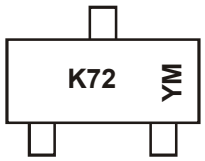
Part Number	Case	Packaging
2N7002W-7-F	SOT-323	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



Chengdu A/T Site



Shanghai A/T Site

K72 = Product Type Marking Code
YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
$\overline{Y}$M = Date Code Marking for CAT (Chengdu Assembly/ Test site)
Y or $\overline{Y}$ = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2012	2013	2014	2015	2016	2017	2018
Code	Z	A	B	C	D	E	F

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0M\Omega$		V_{DGR}	60	V
Gain-Source Voltage	Continuous Pulsed	V_{GSS}	±20 ±40	V
Drain Current (Note 5)	Continuous Continuous @ +100°C Pulsed	I_D	115 73 800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5) Derating above T_A = +25°C	P_D	200 1.60	mW mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage		BV_{DSS}	60	70	—	V	V_{GS} = 0V, I_D = 10μA
Zero Gate Voltage Drain Current @ T_C = +125°C	@ T_C = +25°C	I_{DSS}	—	—	1.0 500	μA	V_{DS} = 60V, V_{GS} = 0V
Gate-Body Leakage		I_{GSS}	—	—	±10	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage		$V_{GS(th)}$	1.0	—	2.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance @ T_j = +125°C	@ T_J = +25°C	$R_{DS(ON)}$	—	1.8 2.6	7.5 13.5	Ω	V_{GS} = 5.0V, I_D = 0.05A V_{GS} = 10V, I_D = 0.5A
On-State Drain Current		$I_{D(ON)}$	0.5	1.0	—	A	V_{GS} = 10V, V_{DS} = 7.5V
Forward Transconductance		g_{FS}	80	—	—	mS	V_{DS} = 10V, I_D = 0.2A
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance		C_{iss}	—	22	50	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance		C_{oss}	—	11	25	pF	
Reverse Transfer Capacitance		C_{rss}	—	2.0	5.0	pF	
SWITCHING CHARACTERISTICS (Note 7)							
Turn-On Delay Time		$t_{D(ON)}$	—	7.0	20	ns	V_{DD} = 30V, I_D = 0.2A, R_L = 150Ω, V_{GEN} = 10V, R_{GEN} = 25Ω
Turn-Off Delay Time		$t_{D(OFF)}$	—	11	20	ns	

Notes:
5. Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to production testing.

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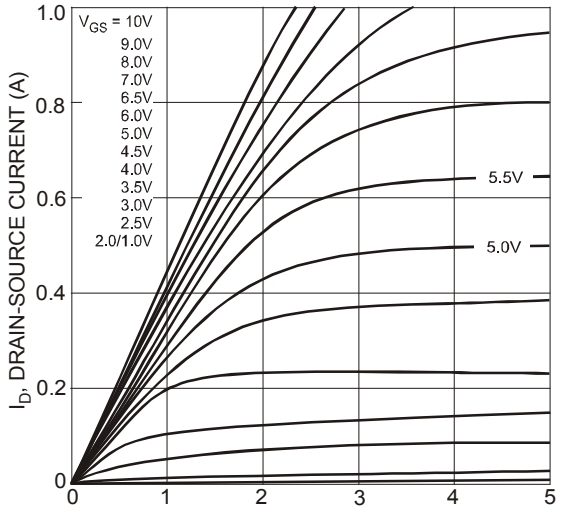


Fig. 1 On-Region Characteristics

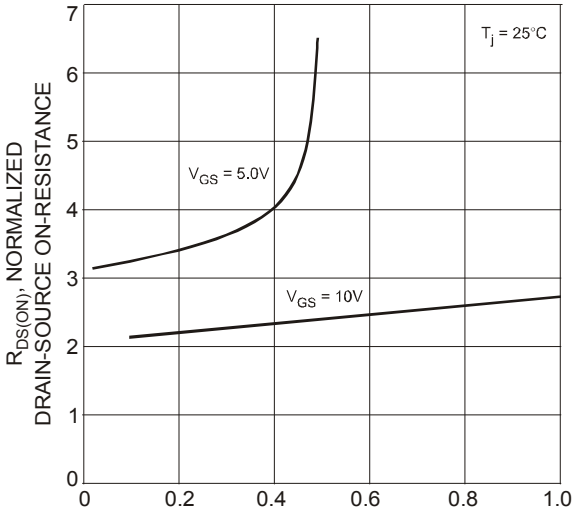


Fig. 2 On-Resistance vs. Drain Current

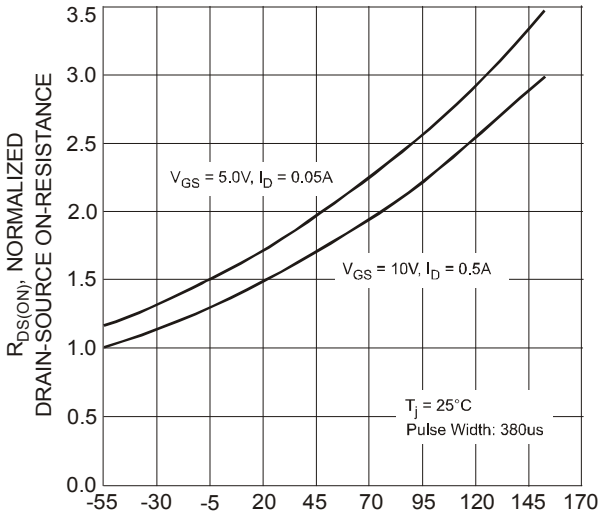


Fig. 3 On-Resistance vs. Junction Temperature

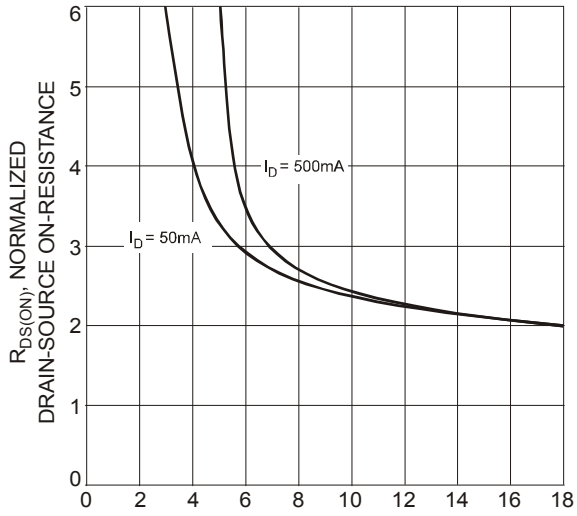
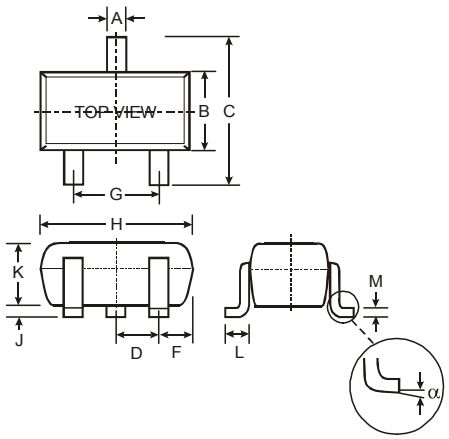


Fig. 4 On-Resistance vs. Gate-Source Voltage

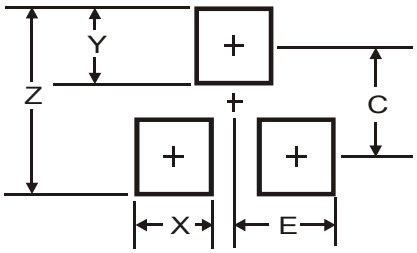
Package Outline Dimensions



SOT-323		
Dim	**Min**	**Max**
A	0.25	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.18
α	0°	8°
All Dimensions in mm		

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Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

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